

ABSTRACT

An integrated circuit having copper interconnecting metallization (311, 312) protected by a first overcoat layer (320), portions of the metallization exposed in windows (301, 302) opened through the thickness of the first overcoat layer. A patterned conductive barrier layer (330) is positioned on the exposed portion of the copper metallization and on portions of the first overcoat layer surrounding the window. A bondable metal layer (350, 351) is positioned on the barrier layer; the thickness of this bondable layer is suitable for wire bonding. A second overcoat layer (360) including insulating silicon compounds is positioned on the first overcoat layer so that the edge (362) of the second overcoat layer overlays the edge of the bondable layer positioned on the portions (321) of the first overcoat layer surrounding the window.